



30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

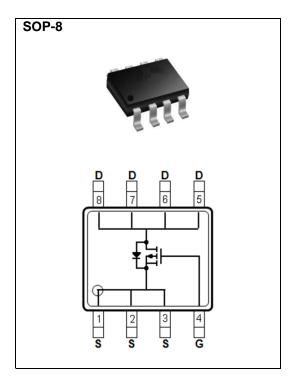
-15A

Features

- R_{DS(ON)}, V_{GS}@-10V, I_D@-15A<4.5mΩ
- $\bullet \;\; R_{DS(ON)} \;, \, V_{GS}@\text{-}4.5V, \, \bar{I}_{D}@\text{-}10A\text{-}7m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)

Mechanical Data

- Case: SOP-8 package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0029 ounces, 0.083 grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _A =25°C	l _D	-15		
	T _A =70°C		-12	Α	
Pulsed Drain Current (Note 1)		I _{DM}	-72	Α	
Power Dissipation	T _A =25°C	P _D	1.7	147	
	T _A =70°C		1.1	W	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance					
- Junction to Ambient (Note 5)		$R_{\theta JA}$	73.5	°C/W	





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1	-1.6	-2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-15A	-	3.9	4.5	mΩ	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V,I _D =-10A	-	5.7	7		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-30V, V_{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	Q_g	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V ^(Note 2,3)	-	107	-	nC	
Gate-Source Charge	Q_gs		-	18	-		
Gate-Drain Charge	Q_gd		-	18	-		
Input Capacitance	Ciss	V _{DS} =-25V, V _{GS} =0V, f=1.0MHZ	-	6067	-	pF	
Output Capacitance	Coss		-	709	-		
Reverse Transfer Capacitance	Crss		-	361	-		
Turn-On Delay Time	td _(on)	\/ 45\/ L 4A	-	22	-	ns	
Turn-On Rise Time	tr	$\begin{array}{c} V_{DS}\text{=-}15V,I_{D}\text{=-}1A,\\ V_{GS}\text{=-}10V,\ R_{G}\text{=}6\Omega\\ \text{(Note 2,3)} \end{array}$	-	48	-		
Turn-Off Delay Time	td _(off)		-	197	-		
Turn-Off Fall Time	tf		-	90	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	-15	А	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =-1A, V _{GS} =0V	-	-0.68	-1.0	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

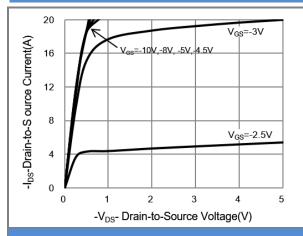


Fig.1 On-Region Characteristics

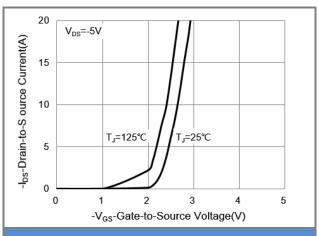


Fig.2 Transfer Characteristics

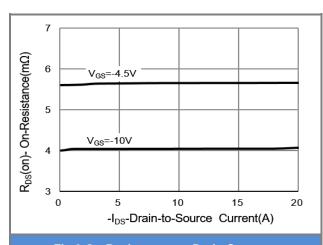


Fig.3 On-Resistance vs. Drain Current

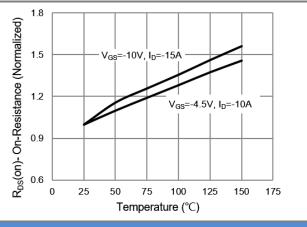


Fig.4 On-Resistance vs. Junction temperature

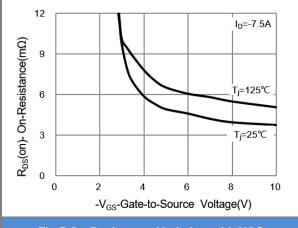


Fig.5 On-Resistance Variation with VGS.

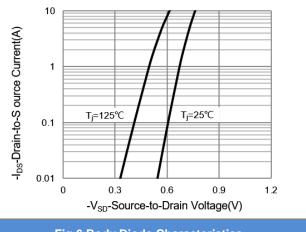


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

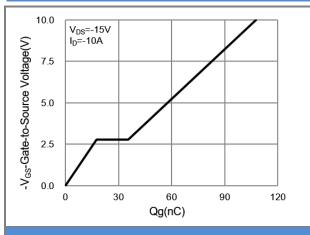


Fig.7 Gate-Charge Characteristics

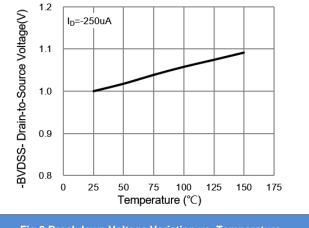


Fig.8 Breakdown Voltage Variation vs. Temperature

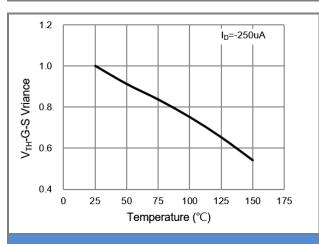


Fig.9 Threshold Voltage Variation with Temperature.

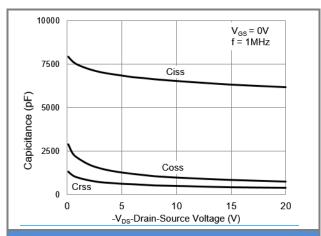


Fig.10 Capacitance vs. Drain-Source Voltage.

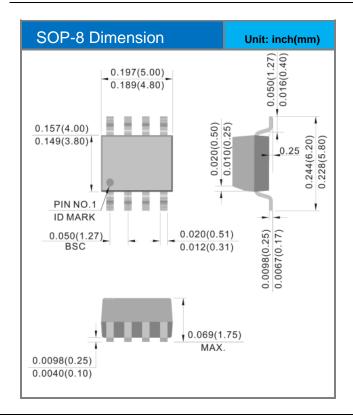


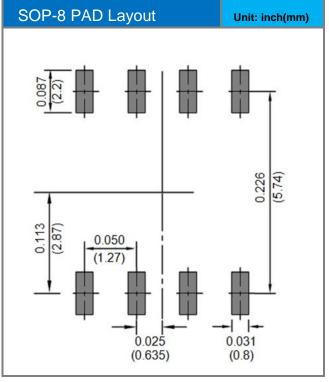


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJL9417_R2_00001	SOP-8	2.5K pcs / 13" reel	L9417	Halogen free

Packaging Information & Mounting Pad Layout









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